

# EPIGAP Optronic GmbH

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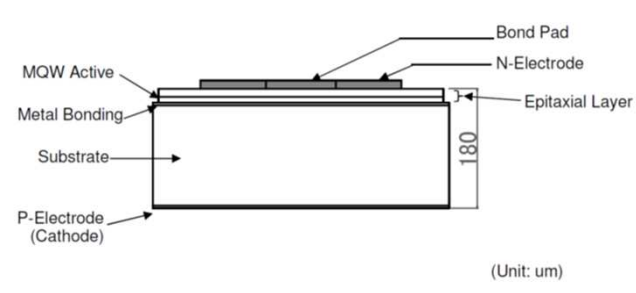
## Data Sheet

### LED Chip Infrared

### EOLC-850-22-1

Rev. 03, 2017

Radiation	Type	Electrodes
Infrared	InAlGaAs epitaxial layer, MQW	n (cathode) up

typ. dimensions	
	<p>typ. die size: 510 x 510 <math>\mu\text{m}</math>                      typ. thickness: 180 <math>\mu\text{m}</math>                      typ. bond pad size: 120 <math>\mu\text{m}</math></p> <p>anode metallization: gold-alloy                      cathode metallization: gold-alloy</p>

### Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 100 \text{ mA}$	$V_F$		1.48		V
Forward voltage	$I_F = 150 \text{ mA}$	$V_F$		1.53		V
Reverse current	$V_R = 5 \text{ V}$	$I_R$			10	$\mu\text{A}$
Radiant power*	$I_F = 100 \text{ mA}$	$\Phi_e$		38		mW
Radiant power*	$I_F = 150 \text{ mA}$	$\Phi_e$		50		mW
Peak wavelength	$I_F = 20 \text{ mA}$	$\lambda_p$		850		nm
FWHM	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		25		nm

\*Measured on epoxy covered chip on TO-18 header

### Packing

Dice on adhesive film with wire bond side up.

Art. No. 113 076



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.